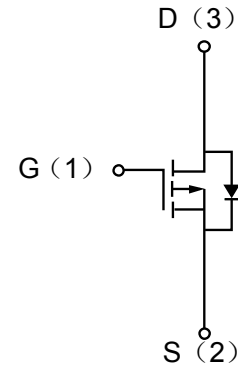


## Description

The enhancement mode MOS is extremely high density cell and low on-resistance.

MOSFET Product Summary		
$V_{DS}(V)$	$R_{DS(on)}(\Omega)$	$I_D(mA)$
-50	10 @ $V_{GS}=-10V$	-130



## Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Drain-Source Voltage	$V_{DS}$	-50	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	-130	mA
Pulsed Drain Current	$I_{DM}$	-520	mA
Total Power Dissipation	$P_{tot}$	250	mW
Storage Temperature Range	$T_{STG}$	-65 to +150	°C
Operating Junction Temperature	$T_J$	150	°C

## Thermal resistance

Parameter	Symbol	Value	Units
Thermal Resistance, Junction-to-Ambient	$R_{th\ j-a}$	500	K/W

Electrical characteristics per line@25°C ( unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D = -10\mu A, V_{GS} = 0V$	-50		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -50V, V_{GS} = 0V$	-	-	-10	$\mu A$
Gate-to-Source Forward Leakage	$I_{GSS}$	$V_{GS} = \pm 20V$	-	-	$\pm 10$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -1mA$	-0.8		-2	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -130mA$			10	$\Omega$
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -25V, I_D = -130mA$	50	-	-	mS
Input Capacitance	$C_{ISS}$	$V_{GS} = 0V, V_{DS} = -25V, f = 1MHz$	-	25	45	pF
Output Capacitance	$C_{DSS}$		-	15	25	pF
Reverse Transfer Capacitance	$C_{RSS}$		-	3.5	12	pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -40V, V_{GS} = -10V, I_D = -200mA$	-	3	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	7	-	

Typical Characteristics

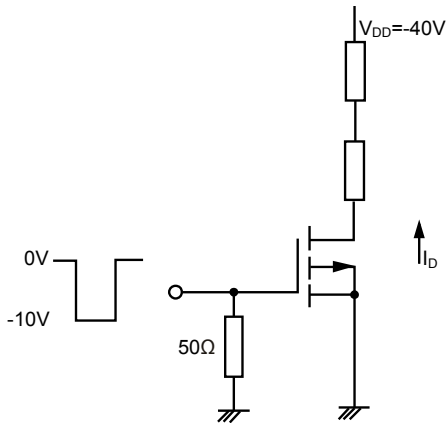


Figure 1. Switching Time Test Circuit

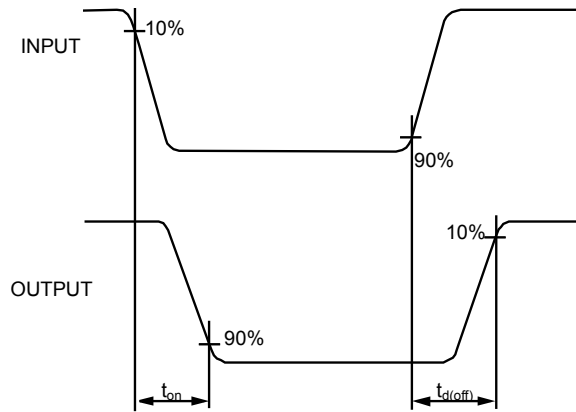


Figure 2. Input and Output Waveforms

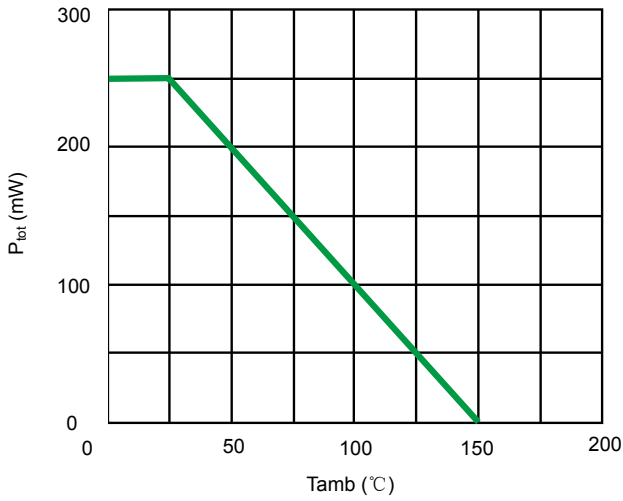


Fig 3. Power Derating Curve

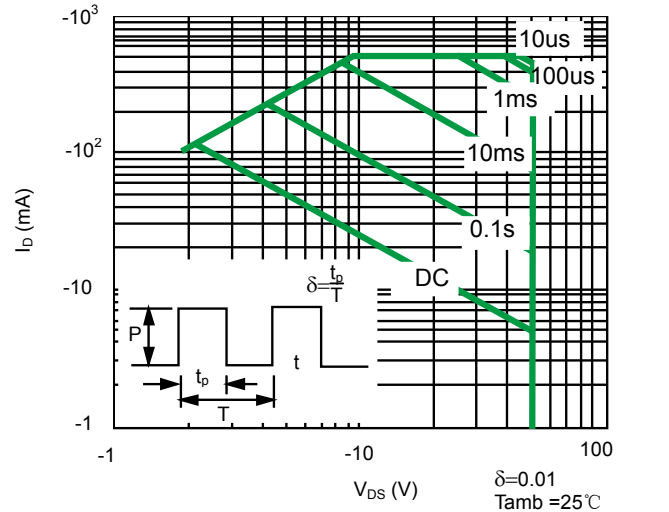


Fig 4. DC SOAR

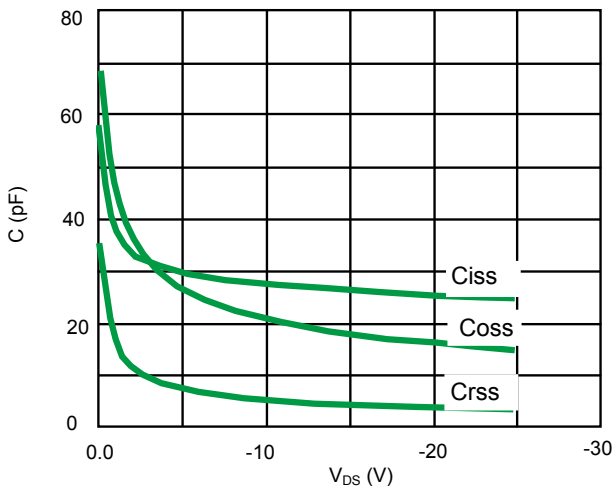


Fig 5. Capacitance

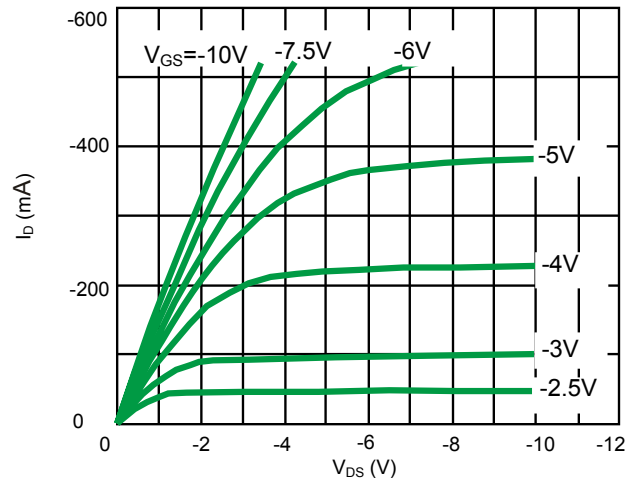


Fig 6. Typical Output Characteristics

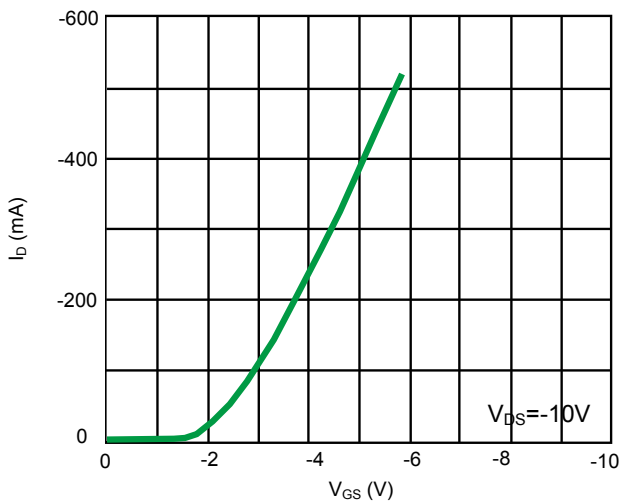


Fig 7. Typical Transfer Characteristics

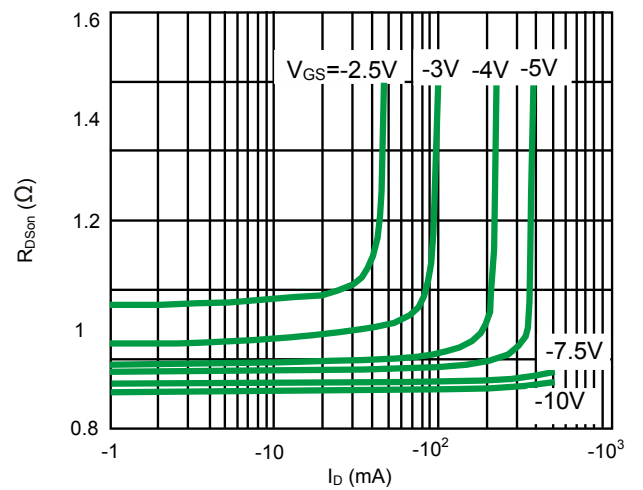


Fig 8. Drain-Source On-State Resistance as a Function of Drain Current; Typical Values

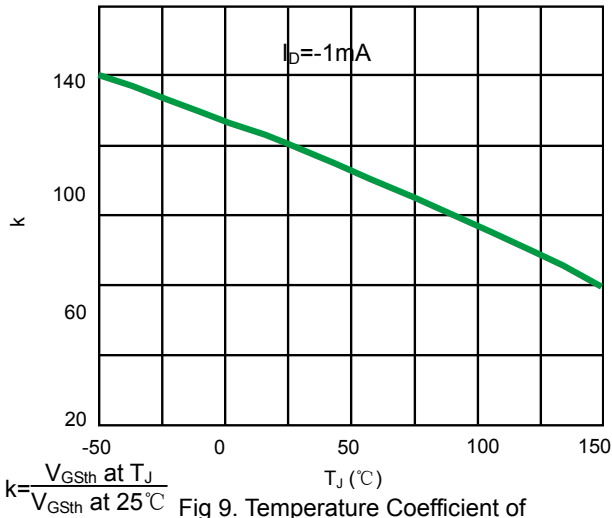


Fig 9. Temperature Coefficient of Gate-Source Threshold Voltage

$$k = \frac{V_{GSth \text{ at } T_J}}{V_{GSth \text{ at } 25^\circ C}}$$

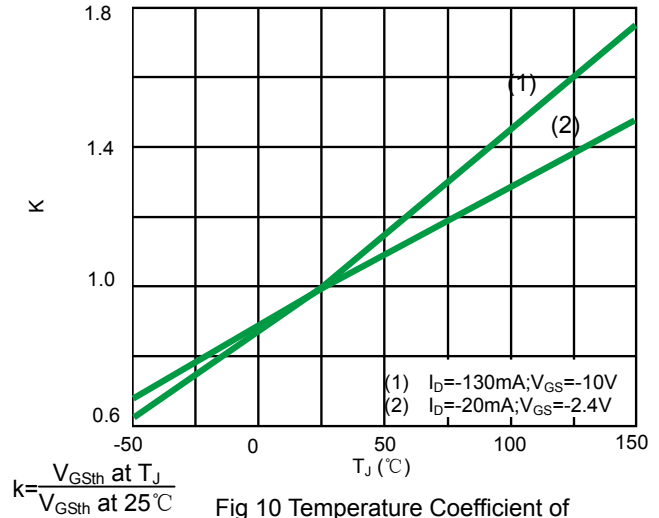


Fig 10 Temperature Coefficient of Drain-Source On-State Resistance

$$k = \frac{V_{GSth \text{ at } T_J}}{V_{GSth \text{ at } 25^\circ C}}$$

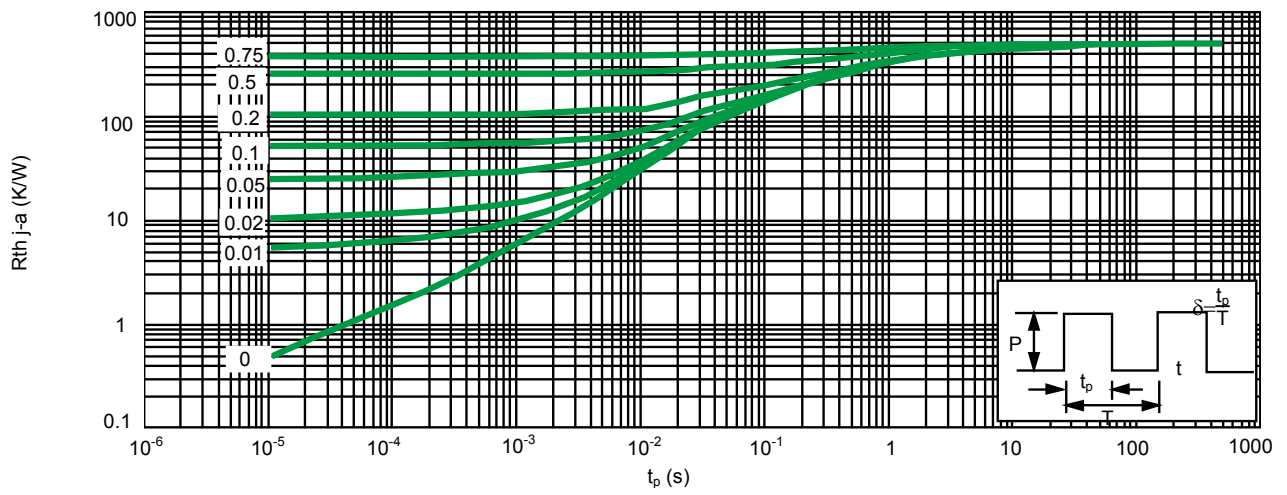
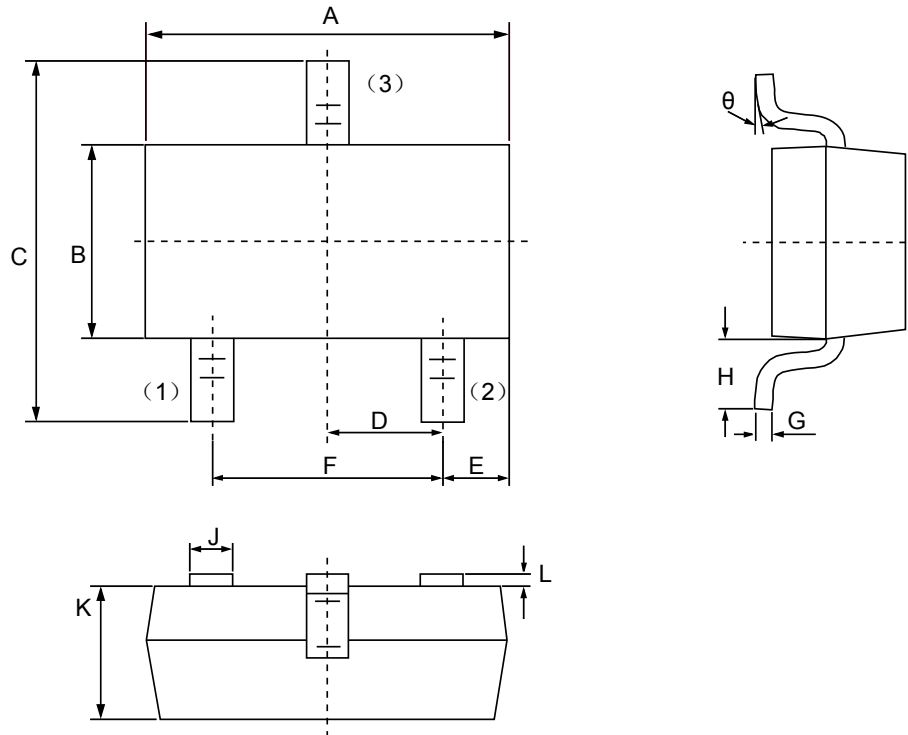



Fig 11. Thermal Resistance From Junction to Ambient as a Function of Pulse Time; Typical Values

Product dimension(SOT-23)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.80	3.00	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	2.10	2.50	0.0830	0.0984
D	0.89	1.02	0.0350	0.0401
E	0.45	0.60	0.0177	0.0236
F	1.78	2.04	0.0701	0.0807
G	0.085	0.177	0.0034	0.0070
H	0.45	0.60	0.0180	0.0236
J	0.37	0.50	0.0150	0.0200
K	0.89	1.11	0.0350	0.0440
L	0.013	0.100	0.0005	0.0040
θ	0°	10°	0°	10°


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